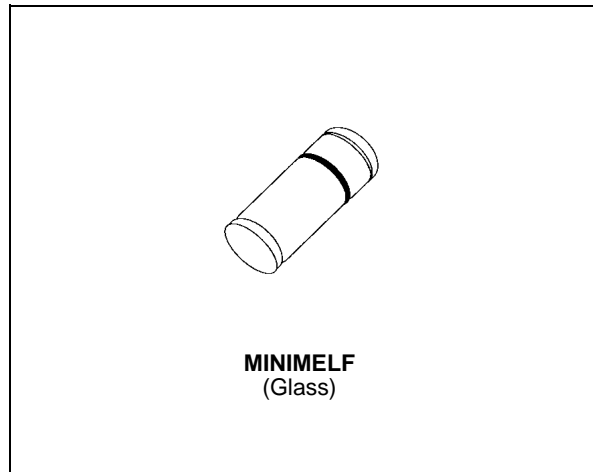


SMALL SIGNAL SCHOTTKY DIODES

**DESCRIPTION**

General purpose, metal to silicon diodes featuring very low turn-on voltage fast switching.

These devices have integrated protection against excessive voltage such as electrostatic discharges.



**ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		30	V
$I_F$	Forward Continuous Current	$T_1 = 25\text{ }^\circ\text{C}$	200	mA
$I_{FRM}$	Repetitive Peak Forward Current	$t_p \leq 1\text{ s}$ $\delta \leq 0.5$	500	mA
$I_{FSM}$	Surge non Repetitive Forward Current	$t_p = 10\text{ ms}$	4	A
$P_{tot}$	Power Dissipation	$T_1 = 65\text{ }^\circ\text{C}$	200	mW
$T_{stg}$ $T_j$	Storage and Junction Temperature Range		- 65 to 150 - 65 to 125	$^\circ\text{C}$ $^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering during 15s		260	$^\circ\text{C}$

**THERMAL RESISTANCE**

Symbol	Test Conditions	Value	Unit
$R_{th(j-l)}$	Junction-leads	300	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS**

**STATIC CHARACTERISTICS**

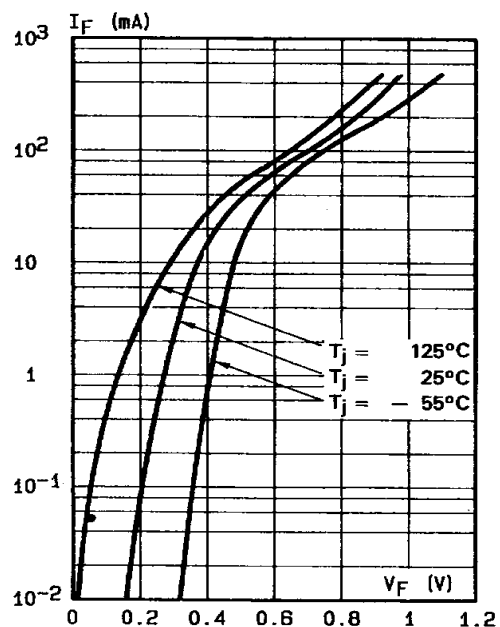
Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$V_{BR}$	$T_j = 25^\circ\text{C}$	$I_R = 100\mu\text{A}$	30			V
$V_F^*$	$T_j = 25^\circ\text{C}$	$I_F = 200\text{mA}$	All Types		1	V
	$T_j = 25^\circ\text{C}$	$I_F = 10\text{mA}$	BAT 42		0.4	
	$T_j = 25^\circ\text{C}$	$I_F = 50\text{mA}$			0.65	
	$T_j = 25^\circ\text{C}$	$I_F = 2\text{mA}$	BAT 43		0.33	
	$T_j = 25^\circ\text{C}$	$I_F = 15\text{mA}$			0.45	
$I_R^*$	$T_j = 25^\circ\text{C}$	$V_R = 25\text{V}$			0.5	$\mu\text{A}$
	$T_j = 100^\circ\text{C}$				100	

**DYNAMIC CHARACTERISTICS**

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	$T_j = 25^\circ\text{C}$	$V_R = 1\text{V}$ $f = 1\text{MHz}$		7		pF
trr	$T_j = 25^\circ\text{C}$	$I_F = 10\text{mA}$ $I_R = 10\text{mA}$ $i_{rr} = 1\text{mA}$ $R_L = 100\Omega$			5	ns
$\eta$	$T_j = 25^\circ\text{C}$	$R_L = 15\text{K}\Omega$ $C_L = 300\text{pF}$ $f = 45\text{MHz}$ $V_i = 2\text{V}$	80			%

\* Pulse test:  $t_p \leq 300\mu\text{s}$   $\delta < 2\%$ .

**Figure 1. Forward current versus forward voltage at different temperatures (typical values).**



**Figure 2. Forward current versus forward voltage (typical values).**

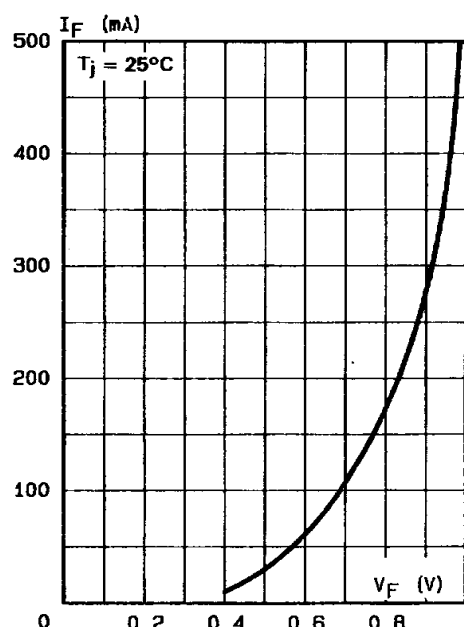


Figure 3. Reverse current versus junction temperature.

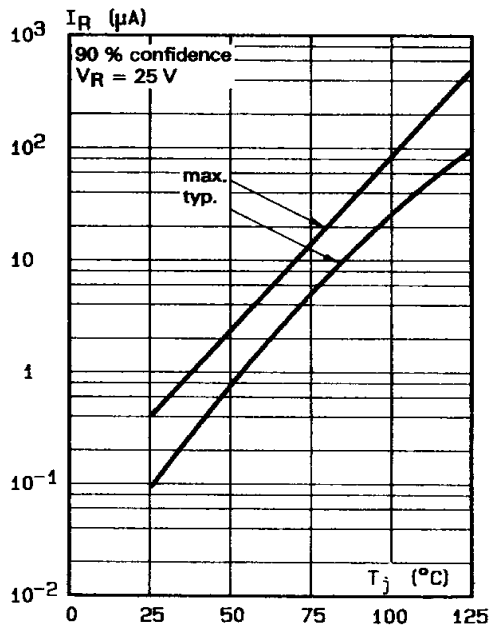


Figure 4. Reverse current versus continuous reverse voltage (typical values).

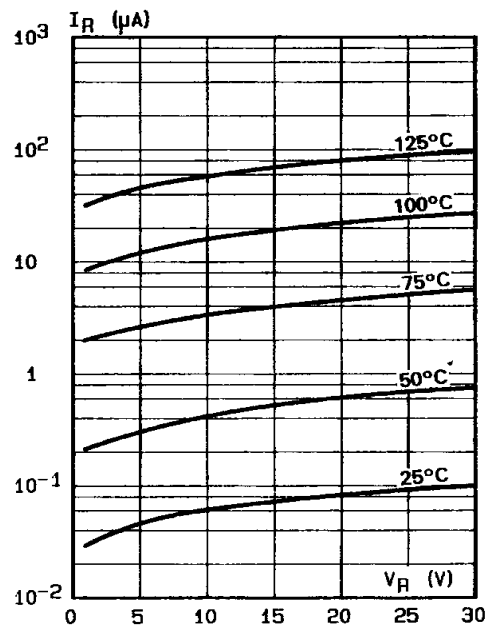
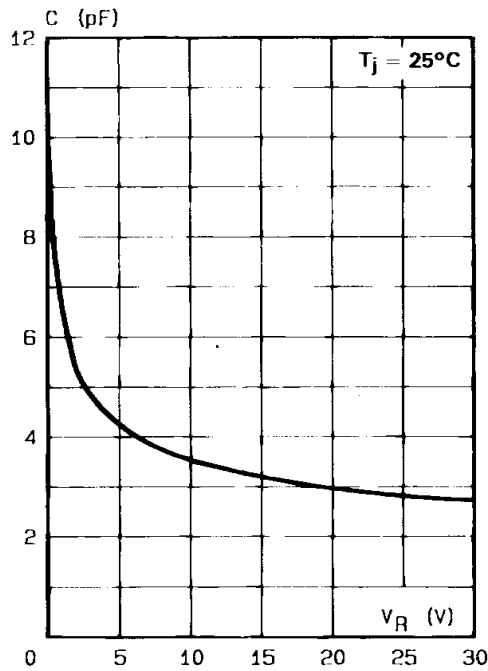


Figure 5. Forward current versus forward voltage (typical values).

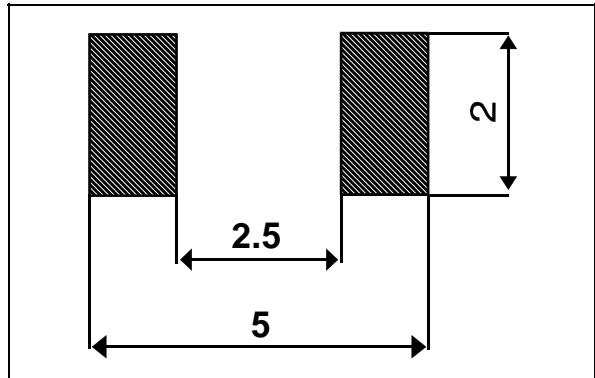
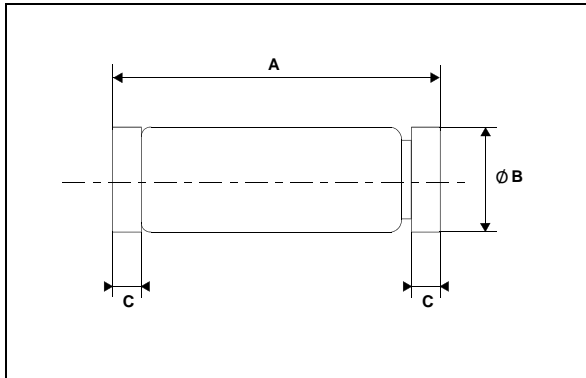


**TMMBAT 42/TMMBAT 43**

**PACKAGE MECHANICAL DATA**

**FOOT PRINT DIMENSIONS (Millimeter)**

MINIMELF Glass



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.3	3.6	0.130	0.142
B	1.59	1.62	0.063	0.064
C	0.4	0.5	0.016	0.020

Marking: ring at cathode end.  
Weight: 0.05g

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